

KDS114WT

SILICON EPITAXIAL PLANAR DIODE

Features

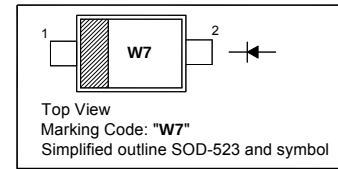
- Small package
- Small total capacitance
- Low series resistance

Applications

- VHF tuner band switch

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

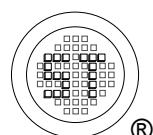


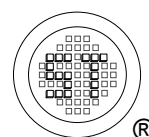
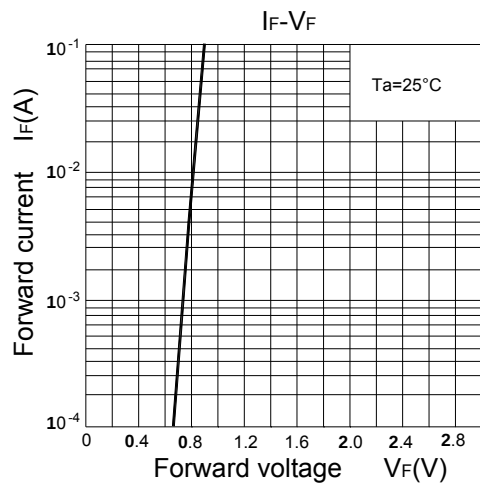
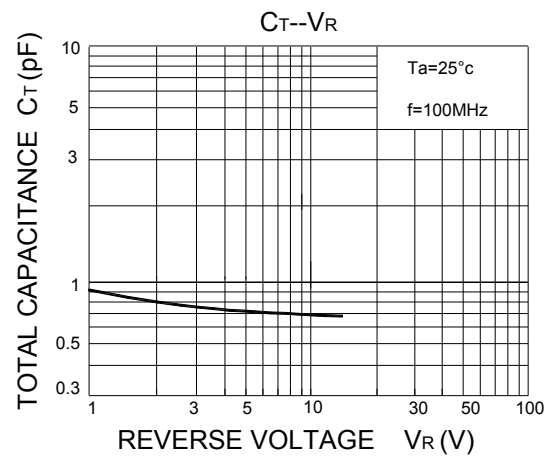
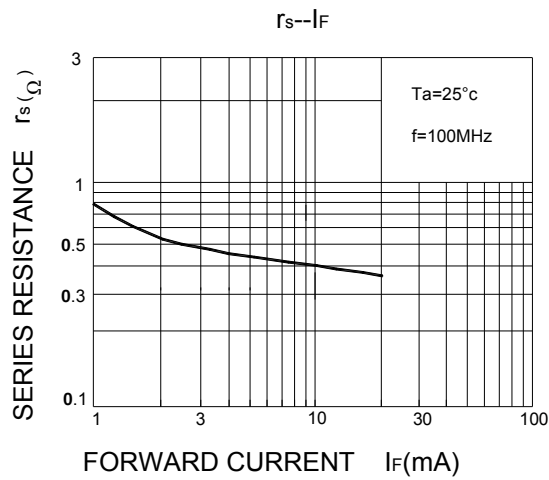
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I_F	100	mA
Junction Temperature Range	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 2 \text{ mA}$	V_F	-	0.85	V
Reverse Current at $V_R = 15 \text{ V}$	I_R	-	0.1	μA
Reverse Voltage at $I_R = 1 \mu\text{A}$	V_R	30	-	V
Total Capacitance at $V_R = 5 \text{ V}$, $f = 1 \text{ MHz}$	C_T	-	1.2	pF
Series Resistance at $I_F = 2 \text{ mA}$, $f = 100 \text{ MHz}$	r_S	-	0.9	Ω



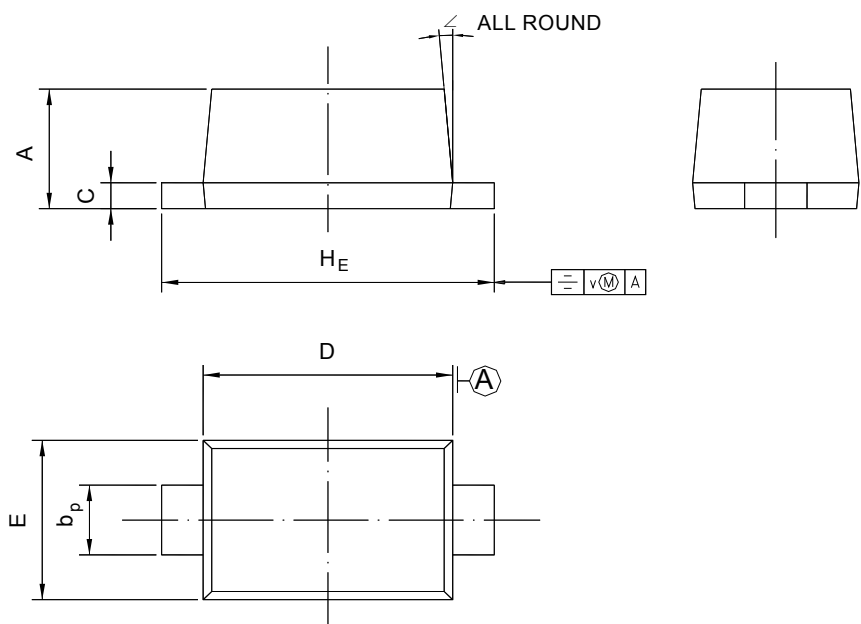


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

